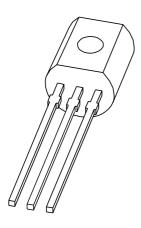
DISCRETE SEMICONDUCTORS

DATA SHEET



PSS9012 series20 V PNP general purpose transistors

Product specification Supersedes data of 2003 May 15 2004 Aug 10





20 V PNP general purpose transistors

PSS9012 series

FEATURES

- High power dissipation: 710 mW
- · Low collector capacitance
- · Low collector-emitter saturation voltage
- · High current capability.

APPLICATIONS

· General purpose switching and amplification.

DESCRIPTION

PNP general purpose transistor in a SOT54 (TO-92) leaded plastic package. NPN complement: PSS9013 series.

MARKING

TYPE NUMBER	MARKING CODE
PSS9012G	S9012G
PSS9012H	S9012H

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	-20	V
I _C	collector current (DC)	-500	mA
I _{CM}	peak collector current	-1	Α

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter

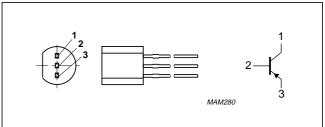


Fig.1 Simplified outline (SOT54; TO-92) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-40	V
V _{CEO}	collector-emitter voltage	open base	_	-20	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-500	mA
I _{CM}	peak collector current		_	-1	Α
I _{BM}	peak base current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	710	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

2

Note

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated and standard footprint.

20 V PNP general purpose transistors

PSS9012 series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	175	K/W

Note

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated and standard footprint.

CHARACTERISTICS

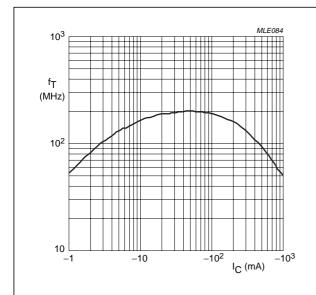
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -35 \text{ V}; I_E = 0$	_	_	-100	nA
		$V_{CB} = -35 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -1 \text{ V; } I_{C} = -500 \text{ mA}$	40	_	_	
h _{FE}	DC current gain	$V_{CE} = -1 \text{ V; } I_{C} = -50 \text{ mA}$				
	PSS9012G		112	_	166	
	PSS9012H		144	_	202	
V _{CEsat}	collector-emitter saturation	$I_C = -100 \text{ mA}; I_B = -10 \text{ mA}$	_	-60	-250	mV
	voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	_	-230	-600	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	_	-1	-1.2	V
V _{BEon}	base-emitter turn on voltage	$V_{CE} = -1 \text{ V; } I_{C} = -100 \text{mA}$	_	-760	-1000	mV
C _c	collector capacitance	$V_{CB} = -6 \text{ V}; I_E = I_e = 0;$ f = 1 MHz	_	6	_	pF

2004 Aug 10 3

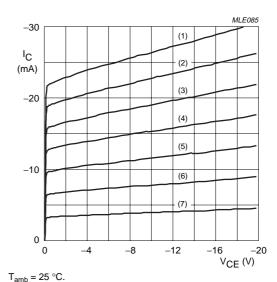
20 V PNP general purpose transistors

PSS9012 series



 $V_{CE} = -6 \text{ V}.$

Fig.2 Transition frequency as a function of collector current; typical values.



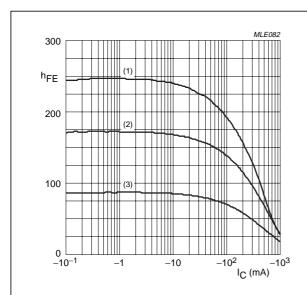
(1) $I_B = -140 \mu A$.

(4) $I_B = -80 \mu A$.

(7) $I_B = -20 \mu A$.

(2) $I_B = -120 \mu A$. (3) $I_B = -100 \mu A$. (5) $I_B = -60 \mu A$. (6) $I_B = -40 \mu A$.

Collector current as a function of collector-emitter voltage; typical values.



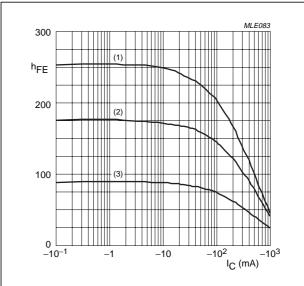
 $V_{CE} = -1 V$.

(1) $T_{amb} = 100 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 DC current gain as a function of collector current; typical values.



 $V_{CE} = -2 V$.

(1) $T_{amb} = 100 \, ^{\circ}C$.

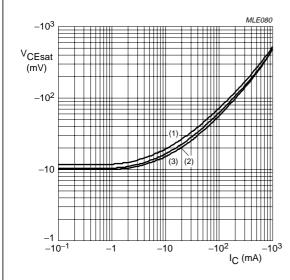
(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 DC current gain as a function of collector current; typical values.

20 V PNP general purpose transistors

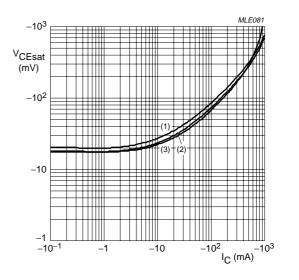
PSS9012 series



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

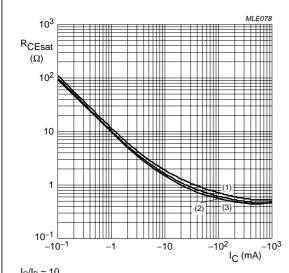
Fig.6 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$

- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

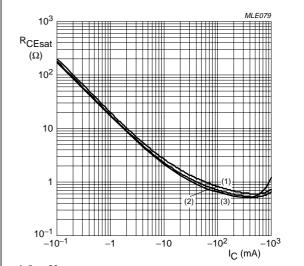
Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_C/I_B = 10$.

- (1) T_{amb} = 100 °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.8 Collector-emitter equivalent on-resistance as a function of collector current; typical values.



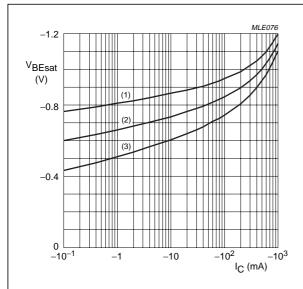
 $I_{\rm C}/I_{\rm B} = 20$.

- (1) $T_{amb} = 25 \, ^{\circ}C$.
- (2) $T_{amb} = 100 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Collector-emitter equivalent on-resistance as a function of collector current; typical values.

20 V PNP general purpose transistors

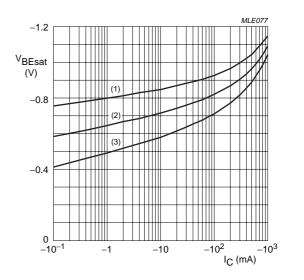
PSS9012 series



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 100 \, ^{\circ}C$.

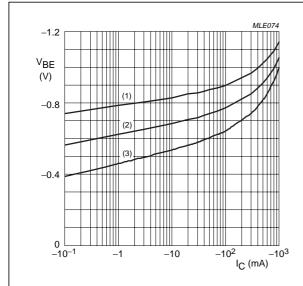
Fig.10 Base-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$.

- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 100 \, ^{\circ}C$.

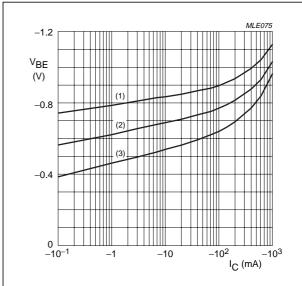
Fig.11 Base-emitter saturation voltage as a function of collector current; typical values.



 $V_{CE} = -1 V$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 100 \, ^{\circ}C$.

Fig.12 Base-emitter voltage as a function of collector current; typical values.



 $V_{CE} = -2 V$.

- (1) $T_{amb} = -55 \,^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 100 \, ^{\circ}C$.

Fig.13 Base-emitter voltage as a function of collector current; typical values.

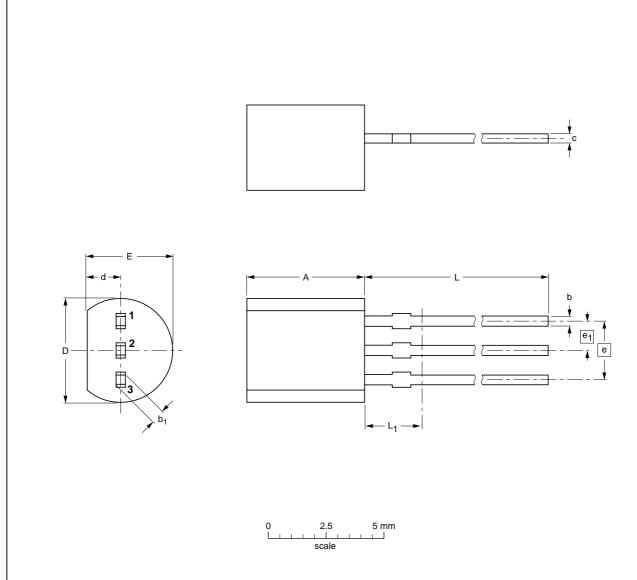
20 V PNP general purpose transistors

PSS9012 series

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE	OUTLINE REFERENCES					ISSUE DATE
VERSION IEC		JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			97-02-28 04-06-28

2004 Aug 10 7

20 V PNP general purpose transistors

PSS9012 series

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LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
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2004 Aug 10 8

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SCA76

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